Sub B9

26. (new) A semiconductor device as in claim 25, wherein the non-volatile memory transistor intermediate insulation layer has a thickness that is identical to that of the gate insulation layer of the third voltage-type transistor.

27. (new) A semiconductor device as in claim 25, wherein the first voltage-type transistor is positioned adjacent to the non-volatile memory transistor, the second voltage-type transistor is positioned adjacent to the first voltage-type transistor, and the third voltage-type transistor is positioned adjacent to the second voltage-type transistor, wherein the first voltage type transistor is positioned between the second voltage type transistor and the non-volatile memory transistor, and wherein the second voltage-type transistor is positioned between the third voltage-type transistor and the first voltage-type transistor.

A(cont

28. (new) A semiconductor device as in claim 21, wherein the first voltage-type transistor operates at a lower voltage range than that of the second voltage-type transistor, and the second voltage-type transistor operates at a lower voltage range than that of the third voltage-type transistor.

Sub B10

29. (new) A semiconductor device as in claim 28, wherein the first voltage-type transistor is positioned adjacent to the non-volatile memory transistor, the second voltage-type transistor is positioned adjacent to the first voltage-type transistor, and the third voltage-type transistor is positioned adjacent to the second voltage-type transistor, wherein the first voltage type transistor is positioned between the second voltage type transistor and the non-volatile memory transistor, and wherein the second voltage-type transistor is positioned between the third voltage-type transistor and the first voltage-type transistor.--

Add B11

REMARKS

This is in response to the Office Action dated November 8, 2001. Applicant has added new claims 24-29. Claims 1-29 are currently pending. Reexamination and reconsideration are respectfully requested.